

isc Silicon NPN Power Transistor

BD933F/935F/937F/939F/941F

DESCRIPTION

- DC Current Gain-
- : h_{FE}= 40(Min)@ I_C= 150mA
- Complement to Type BD934F/936F/938F/940F/942F
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

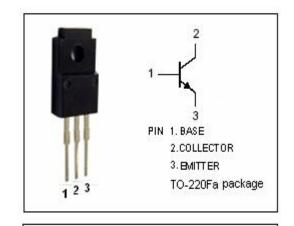
 Designed for use in output stages of audio and television amplifier circuits where high peak powers can occur.

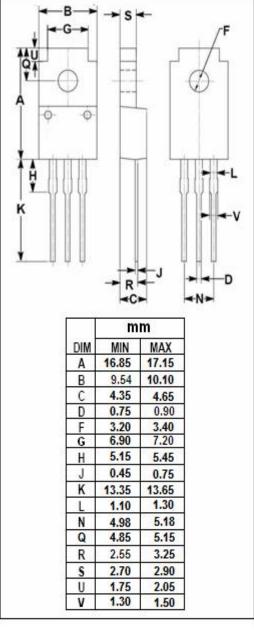
ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)									
SYMBOL	PARAMETER	VALUE	UNIT						
		BD933F	45	V					
V _{СВО}		BD935F	60						
	Collector-Base Voltage	BD937F	100						
		BD939F	120						
		BD941F	140						
V _{CEO}	Collector-Emitter Voltage	BD933F	45						
		BD935F	60						
		BD937F	80	V					
		BD939F	100						
		BD941F	120						
V _{EBO}	Emitter-Base Voltage	5	V						
Ic	Collector Current-Continuo	3	Α						
Ісм	Collector Current-Peak	7	Α						
I _B	Base Current-Continuous	0.5	Α						
Pc	Collector Power Dissipatio @ T _C =25°C	19	W						
TJ	Junction Temperature	150	$^{\circ}$						
T _{stg}	Storage Temperature Ran	-65~150	$^{\circ}\!$						

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	4.17	°C/W
R _{th j-a}	Thermal Resistance, Junction to Ambient	55	°C/W







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ELECTRICAL CHARACTERISTICS

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	BD933F		45			
		BD935F		60			
		BD937F	I _C = 30mA ; I _B = 0	80			V
		BD939F		100			
		BD941F		120			
V _{CE(sat)}	Collector-Emitter Saturation Voltage		I _C = 1A; I _B = 0.1A			0.6	V
$V_{\text{BE(on)}}$	Base-Emitter On Voltage		I _C = 1A; V _{CE} = 2V			1.3	V
I _{CBO}	Collector Cutoff Current		$V_{CB} = V_{CBOmax}$; $I_E = 0$ $V_{CB} = V_{CBOmax}$; $I_E = 0$, $T_J = 150$ °C			0.1 3.0	mA
I _{CEO}	Collector Cutoff Current		V _{CE} = V _{CEOmax} ; I _B = 0			0.5	mA
I _{EBO}	Emitter Cutoff Current		V _{EB} = 5V; I _C = 0			1.0	mA
h _{FE-1}	DC Current Gain		Ic= 150mA ; VcE= 2V	40		250	
h _{FE-2}	DC Current Gain		I _C = 1A; V _{CE} = 2V	25			

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